



### **N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Features**

- Low On-Resistance
  - $25m\Omega$  @  $V_{GS} = 4.5V$
  - $29m\Omega$  @  $V_{GS} = 2.5V$
  - $36m\Omega$  @  $V_{GS} = 1.8V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

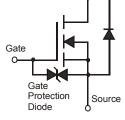
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

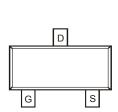








Drain



Top View

Internal Schematic

Top View

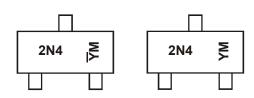
### **Ordering Information** (Note 5)

Part Number	nber Compliance Case		Packaging	
DMG6968U-7	Standard	SOT23	3000/Tape & Reel	
DMG6968UQ-7	Automotive	SOT23	3000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

### **Marking Information**



2N4 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or  $\overline{\gamma}$  = Year (ex: A = 2013) M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

Date Code Kev

Year	2009	9	2010		2011	20	12	2013		2014	2	2015
Code	W		X		Υ	2	7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characte	eristic		Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6)	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	6.5 5.2	А	
Pulsed Drain Current			I <sub>DM</sub>	30	Α

## **Thermal Characteristics**

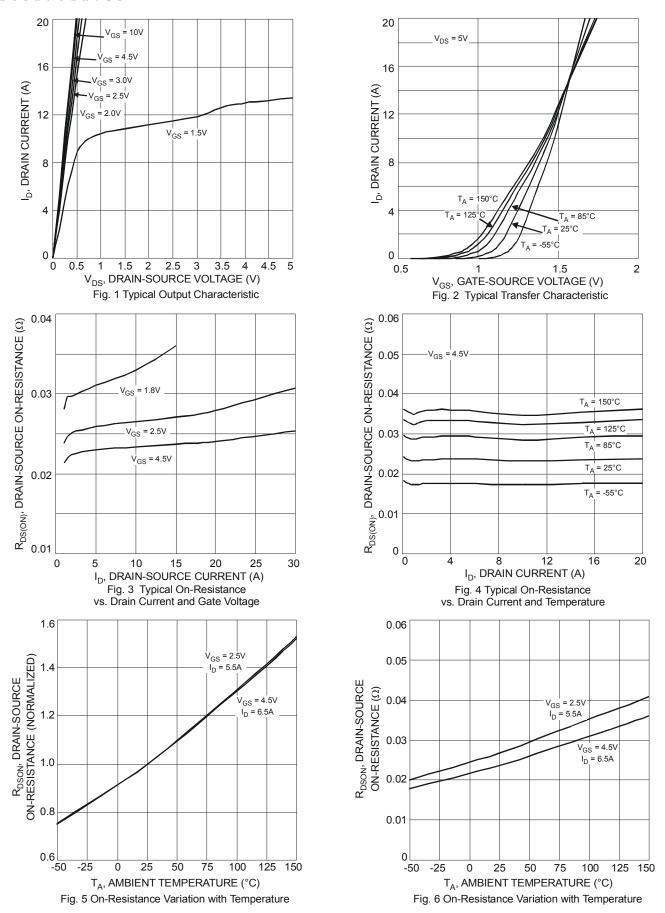
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	1.3	W
Thermal Resistance, Junction to Ambient @ T <sub>A</sub> = +25°C	$R_{\theta JA}$	157	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Syllibol	IVIIII	Тур	IVIAX	Onit	rest Condition		
•	D) /	20	1	1	.,	N/ 01/ 1 050: A		
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	20	_		V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	
Zero Gate Voltage Drain Current	$T_J = +25^{\circ}C$	I <sub>DSS</sub>	_	—	1.0	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage		I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	
Gate-Source Breakdown Voltage		BV <sub>SGS</sub>	±12	_	_	V	$V_{DS} = 0V, I_{G} = \pm 250 \mu A$	
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage		V <sub>GS(th)</sub>	0.5	_	0.9	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			_	21	25		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 6.5A	
Static Drain-Source On-Resistance		R <sub>DS(ON)</sub>		23	29	mΩ	V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 5.5A	
				28	36		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 3.5A	
Forward Transfer Admittance			_	8	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 5A	
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>	)							
Input Capacitance		C <sub>iss</sub>	_	151	_	pF		
Output Capacitance		Coss	_	91	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance		Crss	_	32	_	pF	1.500112	
Total Gate Charge		Qg	_	8.5	_	nC		
Gate-Source Charge		Q <sub>gs</sub>	_	1.6	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.5A$	
Gate-Drain Charge		$Q_{gd}$	_	2.8	_	nC		
Turn-On Delay Time		t <sub>D(on)</sub>	_	54	_	ns		
Turn-On Rise Time		t <sub>r</sub>	_	66	_	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V,	
Turn-Off Delay Time		t <sub>D(off)</sub>	_	613	_	ns	$R_L = 10\Omega$ , $R_G = 6\Omega$ , $I_D = 1A$	
Turn-Off Fall Time	t <sub>f</sub>	_	205	_	ns			

6. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal vias to bottom layer 1 inch square copper plate.7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to production testing. Notes:







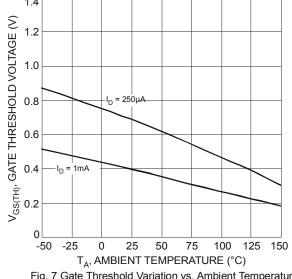
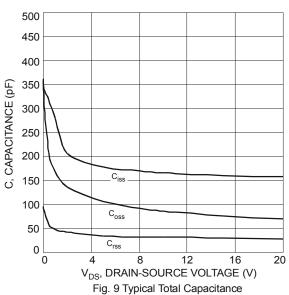
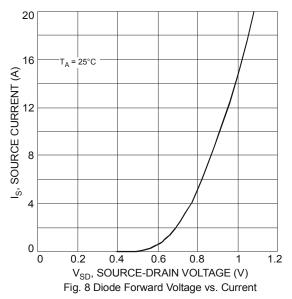


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





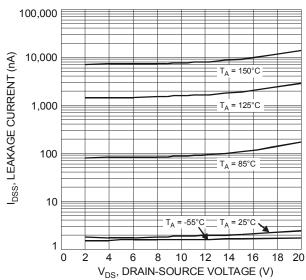


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

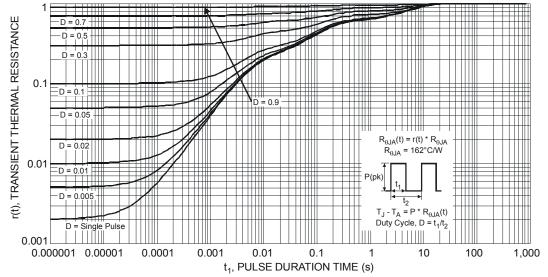
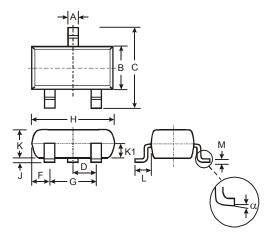


Fig. 11 Transient Thermal Response



# **Package Outline Dimensions**

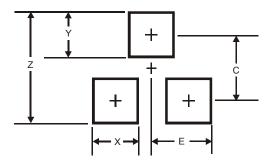
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
М	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)			
Z	2.9			
X	0.8			
Y	0.9			
С	2.0			
F	1.35			



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